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APPLICATION NO.	ı	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/772,585	10/772,585 02/06/2004		Tetsuro Asano	492322017600	2331
25227	7590	09/06/2006		EXAM	INER
		ERSTER LLP	SCHILLINGER, LAURA M		
1650 TYSO SUITE 300	NS BOU	LEVARD		ART UNIT	PAPER NUMBER
MCLEAN,	VA 221	02		2813	***
				DATE MAILED: 09/06/2006	6

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)			
		10/772,585	ASANO ETAL			
	Office Action Summary	Examiner	Art Unit			
		Laura M. Schillinger	2813			
eriod fo	The MAILING DATE of this communication app or Reply	ears on the cover sheet with	the correspondence address			
	ORTENED STATUTORY PERIOD FOR REPLY	/ IS SET TO EXPIRE 2 MOI	NTU(S) OR THIRTY (30) DAVS			
WHIC - Exte after - If NC - Failu Any	CHEVER IS LONGER, FROM THE MAILING DA insions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period we ure to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing led patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICA 36(a). In no event, however, may a repl vill apply and will expire SIX (6) MONTH cause the application to become ABAN	ATION. y be timely filed S from the mailing date of this communication. IDONED (35 U.S.C. § 133).			
tatus						
1)  🏹	Responsive to communication(s) filed on 04 M	av 2006.				
		action is non-final.				
3)	)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits i					
	closed in accordance with the practice under E	x parte Quayle, 1935 C.D.	11, 453 O.G. 213.			
Disposit	ion of Claims					
4)	Claim(s) 1-40 is/are pending in the application.					
	4a) Of the above claim(s) <u>2 and 10-40</u> is/are wi					
	Claim(s) is/are allowed.					
	Claim(s) 1 and 3-9 is/are rejected.					
7)	Claim(s) is/are objected to.					
8)[	Claim(s) are subject to restriction and/or	r election requirement.				
pplicati	ion Papers					
9)	The specification is objected to by the Examine	r				
	The drawing(s) filed on is/are: a) acce		the Examiner.			
	Applicant may not request that any objection to the					
	Replacement drawing sheet(s) including the correcti	- · · · · · · · · · · · · · · · · · · ·	• •			
11)	The oath or declaration is objected to by the Ex	_				
riority ι	under 35 U.S.C. § 119					
12)🖂	Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 1	19(a)-(d) or (f).			
	⊠ All b) ☐ Some * c) ☐ None of:	, , , , , , , , , , , , , , , , , , ,	(-) (-)			
	1. Certified copies of the priority documents	s have been received.				
	2. Certified copies of the priority documents		olication No			
	3. Copies of the certified copies of the prior	ity documents have been re	eceived in this National Stage			
	application from the International Bureau	(PCT Rule 17.2(a)).				
* 5	See the attached detailed Office action for a list	of the certified copies not re	ceived.			
ttachmen	at(s)					
_	ce of References Cited (PTO-892)	4) 🗍 Interview Sun	nmary (PTO-413)			
) 🔲 Notic	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO/SB/08)	Paper No(s)/I	Mail Date rmal Patent Application			

#### **DETAILED ACTION**

# Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims1, 4-9 are rejected under 35 U.S.C. 102(b) as being anticipated by Tohyama (\*323).

Tohyama teaches the following claim limitations as cited below:

1. A semiconductor device comprising;

a substrate (Fig.8 (2));

a plurality of electrodes provided for an operating region formed in the substrate (Fig.8 (8A and 8B));

a plurality of electrode pads formed on the substrate and each connected to a

corresponding electrode of the operating region (Fig.8 (bonding pad));

a plurality of wiring connections between one of the electrodes and a corresponding

electrode pad (Fig.8 (6)); and

a protecting element formed along each of the wiring connections and comprising a first

Art Unit: 2813

high concentration impurity region formed in the substrate (7), a second high concentration impurity region formed in the substrate (5) and an insulating region between the first and second high concentration impurity regions (3), the protecting element being connected between two electrodes of the plurality of electrodes (8A and B) (Fig.8).

- 4. The semiconductor device of claim 1 or 2, wherein each of the protecting elements is disposed adjacent one of the electrode pads (Fig.8).
- 5. The semiconductor device of claim 1 or 2, wherein one of the first and second high concentration impurity regions is connected to part of one of the electrode pads or part of a metal wiring connection connected to one of the electrodes (Fig.8 (7 or 5).
- 6 The semiconductor device of claim 1 or 2, wherein one of the first and second high concentration impurity regions is connected to one of the wiring connections (Fig.8 (7 or 5)).
- 7. The semiconductor device of claim 1 or 2, further comprising a third high concentration impurity region disposed at a periphery of one of the electrode pads, wherein one of the first and second high concentration impurity regions comprises part of the third high concentration impurity region (Fig.8 (7)- this region can be considered both the second and third concentration region since the second comprises the third).

8. The semiconductor device of claim 1 or 2, wherein one of the wiring connections comprises a resistor (Fig.7 (4)).

9. The semiconductor device of claim 1 or 2, wherein one of the first and second high concentration impurity regions comprises part of one of the wiring connections (Fig.8 (7 or 5)).

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Tohyama ('323). Tohyama teaches the limitations of claim 1, however fails to compare the breakdown voltage of a circuit with a protection device to a circuit without one to see if the protection aids by 20 volts or more as claimed by the Applicant. However it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Tohyama's teachings to include such a feature because the protection device taught by Tohyama is to assist in achieving breakdown voltage protection.

## Response to Arguments

Applicant's arguments filed 4/25/06 have been fully considered but they are not persuasive. Applicant argues that wiring layer 6 is not a high concentration impurity region- the

Art Unit: 2813

Examiner agrees; it is noted that the reference numeral (6) indicated by the Examiner in the non final was a typo. However, Applicant had notice that this would be a typo because there was a clear discrepancy of the citations provided for claims 4-5 and 9 which cited 5 and 7 as the first and second high concentration impurity regions. In addition, element 6 is cited as being an electrode pad. Moreover, Applicant is responsible for the reference as a whole and not merely the citations provided by the Examiner. Lastly, elements 5 and 7 constitute high concentration impurity regions within the substrate as claimed.

#### Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

01/22/06

Laura M Schillinger
Primary Examiner
Art Unit 2813